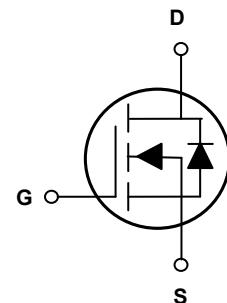
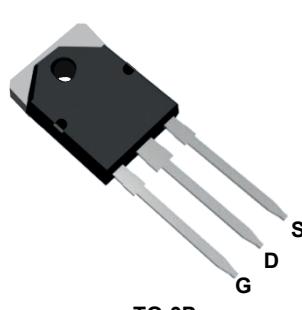


Main Product Characteristics

$V_{(BR)DSS}$	650V
$R_{DS(ON)}$	110mΩ (max.)
I_D	35A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSJV65RF110 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Parameter	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-to-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current, @ Steady-State ($T_C=25^\circ\text{C}$)	I_D	35	A
Continuous Drain Current, @ Steady-State ($T_C=100^\circ\text{C}$)		12	A
Pulsed Drain Current	I_{DM}	140	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	278	W
		2.23	W/ $^\circ\text{C}$
Single Pulse Avalanche Energy ¹	E_{AS}	1136	mJ
Body Diode Reverse Voltage Slope ²	dv/dt	50	V/ns
MOS dv/dt Ruggedness ³	dv/dt	50	V/ns
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction-to-Case	$R_{\theta JC}$	0.45	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_D=250\mu\text{A}$	650	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=650\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-to-Source Forward Leakage	I_{GSS}	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=20\text{V}$	-	-	100	nA
		$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=-20\text{V}$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}, I_D=17\text{A}$	-	90	110	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250\mu\text{A}$	3.1	-	4.9	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=100\text{V}, f=1\text{MHz}$	-	3011	-	pF
Output Capacitance	C_{oss}		-	84	-	
Reverse Transfer Capacitance	C_{rss}		-	5.5	-	
Total Gate Charge ^{4,5}	Q_g	$I_D=19\text{A}, V_{\text{DD}}=480\text{V}, V_{\text{GS}}=10\text{V}$	-	81	-	nC
Gate-to-Source Charge ^{4,5}	Q_{gs}		-	28	-	
Gate-to-Drain ("Miller") Charge ^{4,5}	Q_{gd}		-	42	-	
Gate-to-Plateau Voltage ^{4,5}	V_{plateau}		-	8.4	-	V
Turn-On Delay Time ^{4,5}	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=400\text{V}, V_{\text{GS}}=10\text{V}, R_G=1.8\Omega, I_D=19\text{A}$	-	24	-	nS
Rise Time ^{4,5}	t_r		-	27	-	
Turn-Off Delay Time ^{4,5}	$t_{\text{d}(\text{off})}$		-	59	-	
Fall Time ^{4,5}	t_f		-	23	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	1.82	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	$T_C=25^\circ\text{C}$, MOSFET symbol showing the integral reverse p-n junction diode.	-	-	35	A
Source Pulse Current	I_{SM}		-	-	140	A
Diode Forward Voltage	V_{SD}	$I_S=19\text{A}, V_{\text{GS}}=0\text{V}$	-	1.1	1.4	V
Reverse Recovery Time ²	T_{rr}	$I_F=19\text{A}, V_{\text{DD}}=400\text{V}, dI_F/dt=100\text{A}/\mu\text{s}$	-	104	-	nS
Reverse Recovery Charge ²	Q_{rr}		-	0.46	-	μC
Reverse Recovery Current ²	I_{rrm}		-	8	-	A

Note:

1. $L=79\text{mH}, V_{\text{DD}}=100\text{V}, R_G=25\Omega$, starting temperature $T_J=25^\circ\text{C}$.
2. $V_{\text{DS}}=0-400\text{V}, I_{\text{SD}} \leq I_S, T_J=25^\circ\text{C}$.
3. $V_{\text{DS}}=0-480\text{V}$.
4. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
5. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

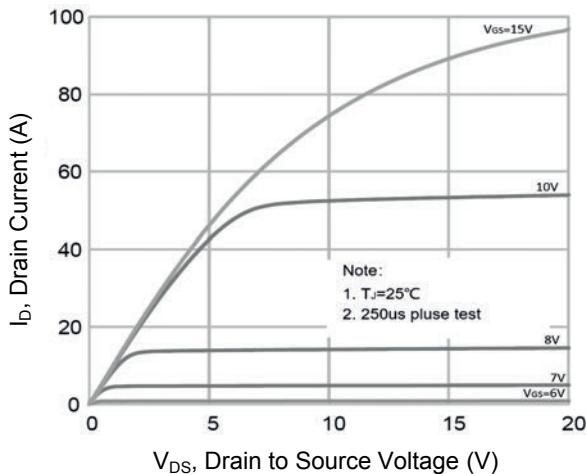


Figure 1. Typical Output Characteristics

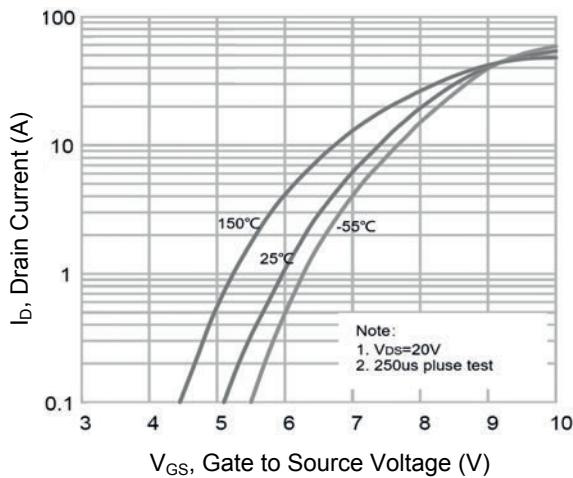


Figure 2. Transfer Characteristics

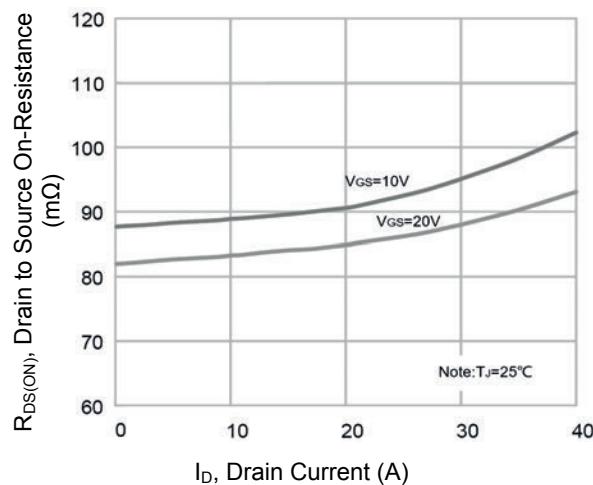


Figure 3. $R_{DS(ON)}$ Vs. Drain Current

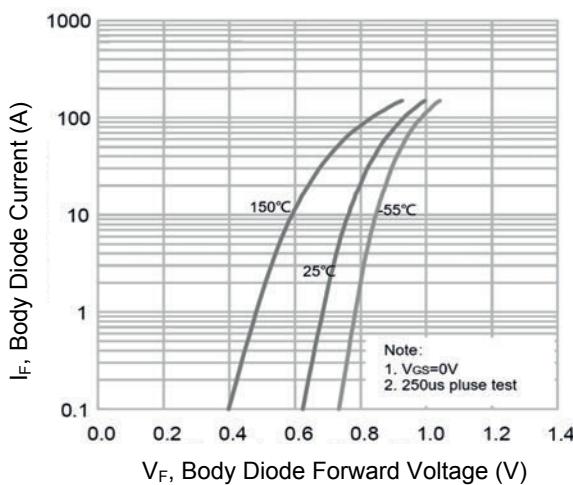


Figure 4. Body Diode Characteristics

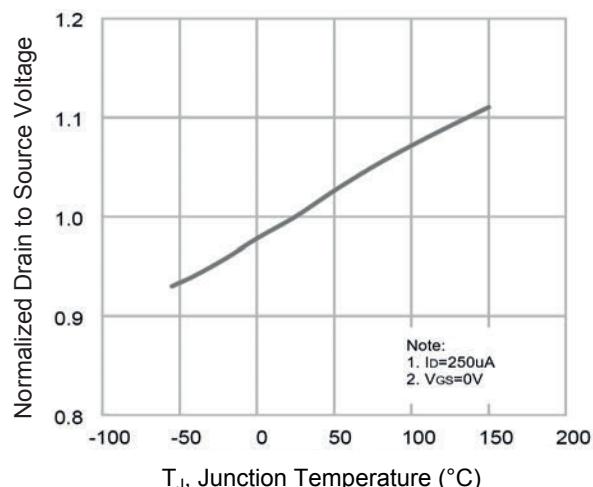


Figure 5. Normalized BV_{DSS} Vs. T_J

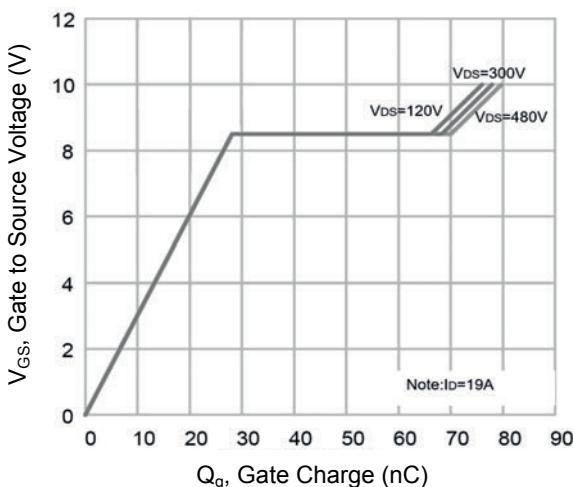


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

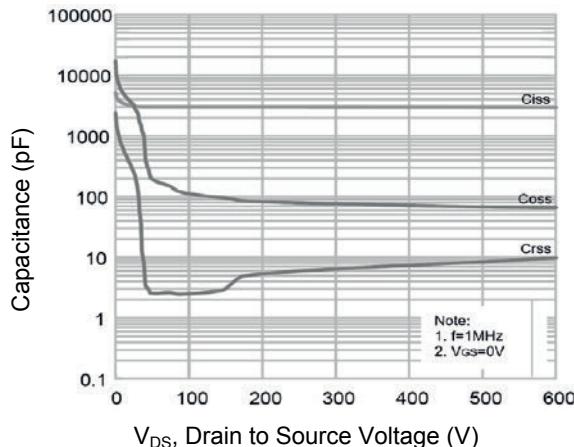


Figure 7. Capacitance Characteristics

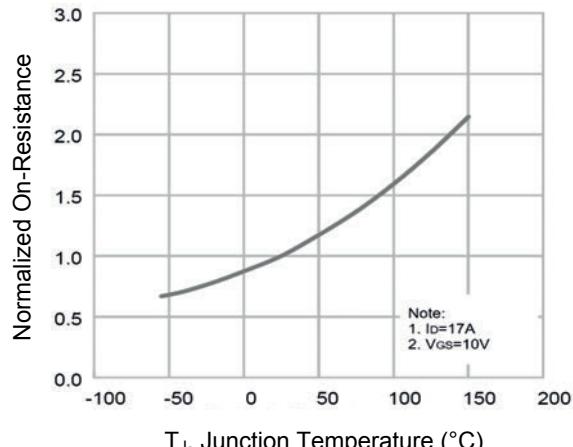


Figure 8. Normalized $R_{DS(ON)}$ Vs. T_J

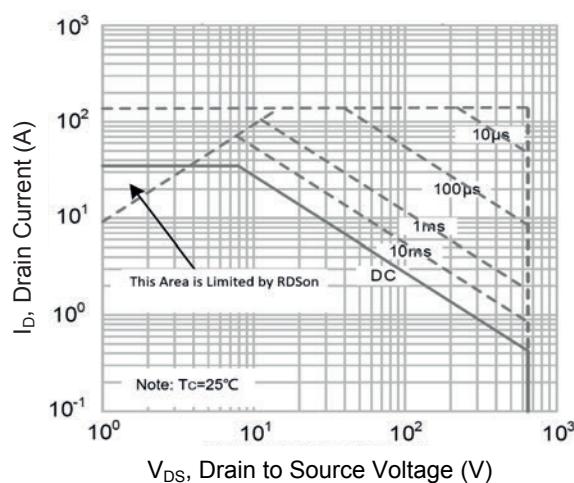
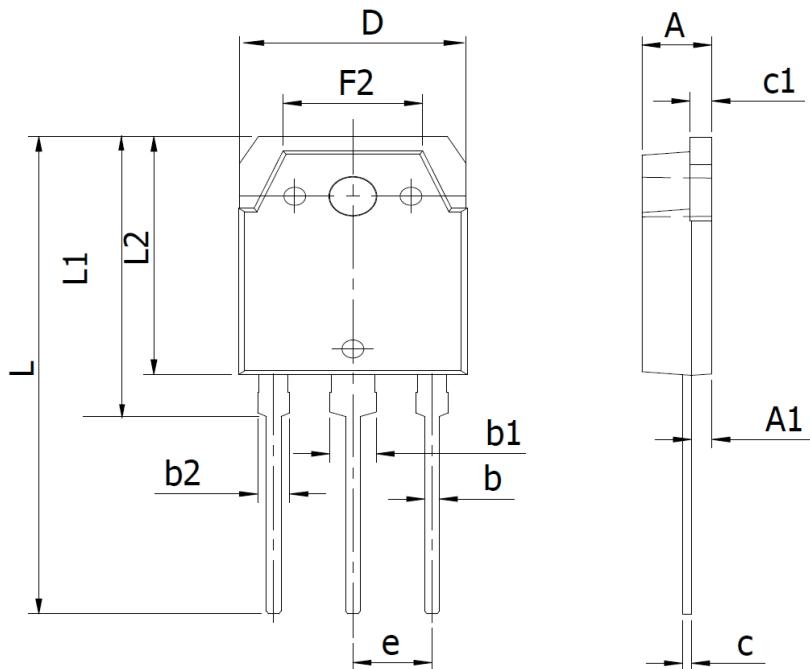


Figure 9. Safe Operation Area

Package Outline Dimensions (TO-3P)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	5.20	0.173	0.205
C1	1.20	1.80	0.047	0.071
A1	1.20	2.00	0.047	0.079
b	0.70	1.30	0.028	0.051
b1	2.70	3.30	0.106	0.130
b2	1.70	2.30	0.067	0.091
D	15.00	16.00	0.591	0.630
C	0.40	0.80	0.016	0.031
F2	8.50	10.00	0.335	0.394
e	5.45 TYP		0.215 TYP	
L1	22.60	23.60	0.890	0.929
L	39.00	41.50	1.535	1.634
L2	19.50	21.00	0.768	0.827